

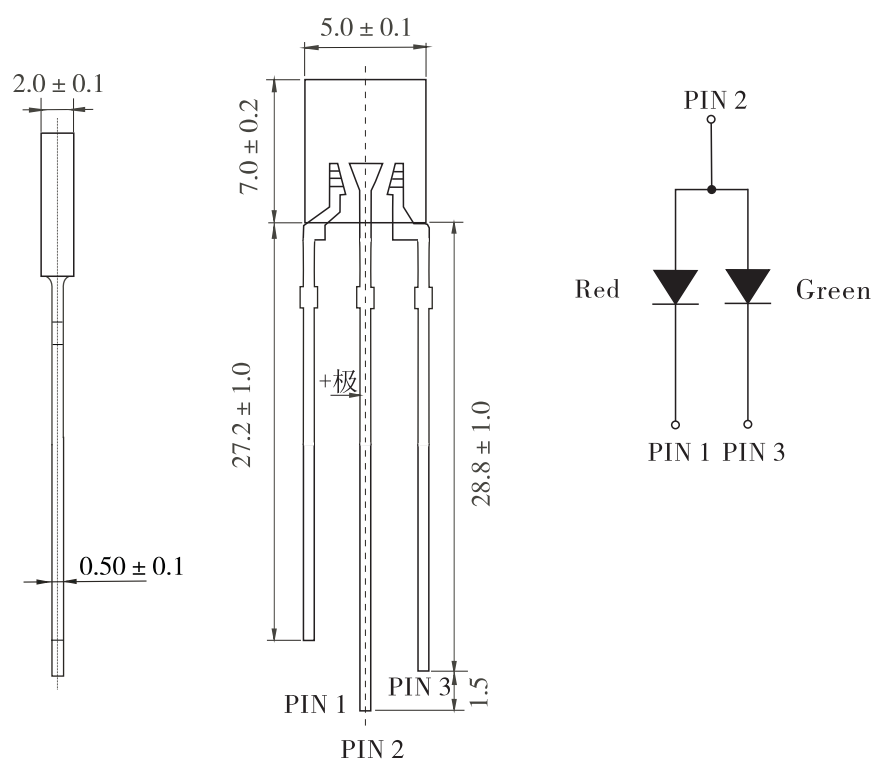
FEATURES

Low power consumption.
High Efficiency
Round type
T1 (3mm) diameter
With Flange
Solder leads without stand-off
Compliant with RoHS

DESCRIPTIONS

Chip Material: AlGaInP/GaAs InGaN/GaN
Emitting Color: Red/Green
Lens Color: Water Clear

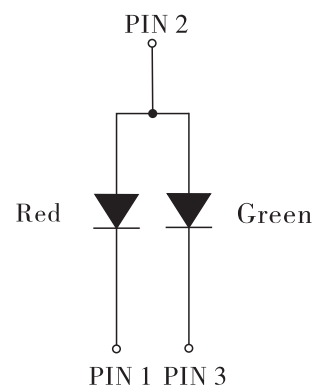
OUTLINE DRAWING



ATTENTION



OBSERVE PRECAUTIONS
FOR HANDLING
ELECTROSTATIC
SENSITIVE DEVICES



Tolerance is ± 0.25 mm
Unless Otherwise Specified.

ELECTRICAL OPTICAL CHARACTERISTICS (Ta=25°C)

Parameter	Symbol	Red			Green			Unit	Test Condition
		Min	Typ	Max	Min	Typ	Max		
Forward Voltage	V_F		2.2	2.5		3.2	3.6	V	IF=20mA
Luminous Intensity	I_V	280	400		500	700		mcd	IF=20mA
Peak Wavelength	λ_P		630			520		nm	IF=20mA
Spectral Line half-width	$\Delta \lambda$		20				30	nm	IF=20mA
Reverse Leakage Current	I_R			50			50	μA	VR=5V
Viewing Angle	$2\theta_{1/2}$		100			100		Deg	IF=20mA

ABSOLUTE MAXIMUM PARAMETERS (Ta=25°C)

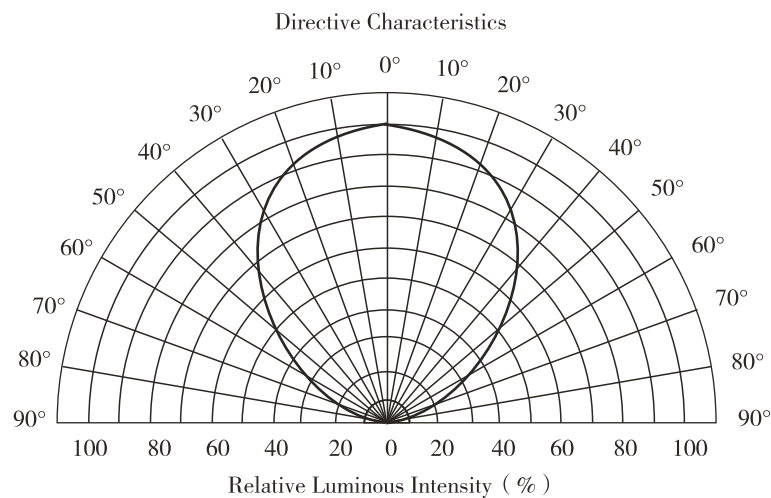
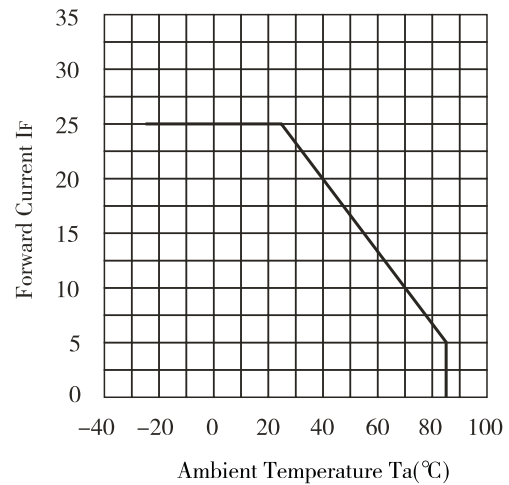
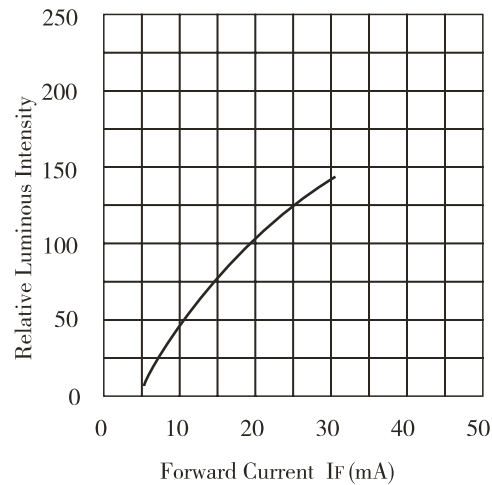
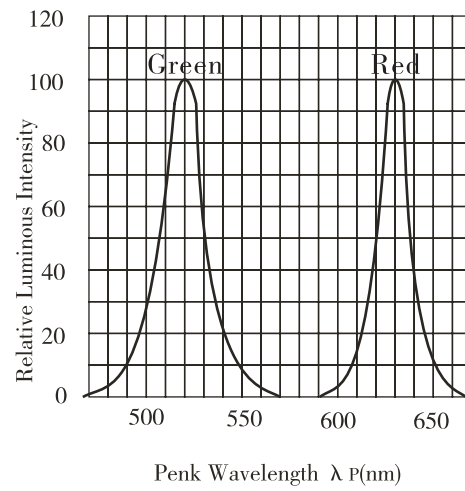
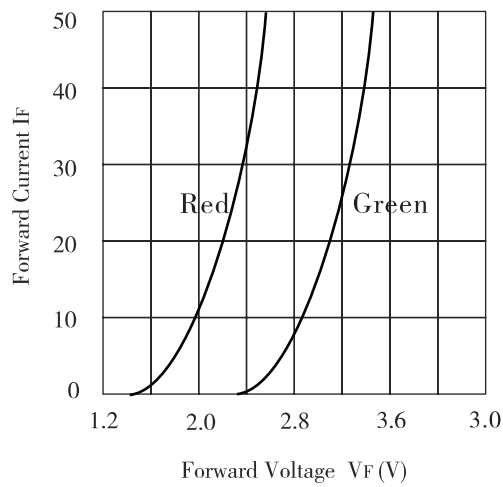
Parameter	Symbol	Condition	Rating	Unit
Power Dissipation	P_D	---	100	mW
Reverse Voltage	V_R	IR=50 μA	5	V
Forward Average Current	I_F	---	30	mA
Temperature coefficient	I/C	---	0.4	mA/ °C
Pulse Current	IFP	Duty=1/10,1kHz	100	mA
Operating Temperature Range	Topr	---	-25 ~ +85	°C
Storage Temperature Range	Tstg	---	-40 ~ +100	°C
Soldering Condition	Tsd	---	265°C/5sec	°C

NOTE:

Luminous Intensity Measurement allowance is $\pm 10\%$.

$2\theta_{1/2}$ is the off-axis angle at which the luminous intensity is half the axial luminous intensity.

The dominant wavelength is derived from the CIE chromaticity diagram and represents the single wavelength which defines the color of the device.

TYPICAL ELECTRO-OPTICAL CHARACTERISTIC CURVES ($T_a=25^{\circ}\text{C}$)


Luminous Intensity Ranks(IF=20mA Ta=25°C)

Bin Code	Min(mcd)	Max(mcd)
N	200	280
P	280	390
Q	390	550
R	550	770
S	770	1100